

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Lu YOU, et al.

Serial No.: 09/785,445

Filed: February 20, 2001

Group Art Unit: 2811

Examiner: H.K. Vu

For: SINGLE DAMASCENE INTEGRATION SCHEME FOR PREVENTING COPPER CONTAMINATION
OF DIELECTRIC LAYER

THE COMMISSIONER FOR PATENTS AND TRADEMARKS
Washington, DC 20231

Dear Sir:

Transmitted herewith is an Amendment in the above identified application.

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No additional fee is required.

Applicant is entitled to small entity status under 37 CFR 1.27

Also attached:

The fee has been calculated as shown below:

	NO. OF CLAIMS	HIGHEST PREVIOUSLY PAID FOR	EXTRA CLAIMS	RATE	FEE
Total Claims	10	30	0	\$18.00 =	\$0.00
Independent Claims	2	4	0	\$84.00 =	\$0.00
Multiple claims newly presented					\$0.00
Fee for extension of time					\$0.00
Total of Above Calculations					\$0.00

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Please charge my Deposit Account No. 500417 in the amount of \$0.00. An additional copy of this transmittal sheet is submitted herewith.

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The Commissioner is hereby authorized to charge payment of any fees associated with this communication or credit any overpayment, to Deposit Account No. 500417, including any filing fees under 37 CFR 1.16 for presentation of extra claims and any patent application processing fees under 37 CFR 1.17.

Respectfully submitted,

MCDERMOTT, WILL & EMERY



Scott D. Paul

Registration No. 42,984

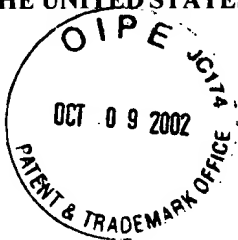
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Date: October 9, 2002

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Docket No.: 50432-022



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H. Vu

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Lu YU, et al.

Application No.: 09/785,445

Group Art Unit: 2811

Filed: February 20, 2001

Examiner: H. Vu

For: SINGLE DAMASCENE INTEGRATION SCHEME FOR PREVENTING COPPER
CONTAMINATION OF DIELECTRIC LAYER

AMENDMENT

Box Non-Fee Amendment
The Commissioner for Patents and Trademarks
Washington, DC 20231

Sir:

The following Amendment and Remarks are submitted in response to the Office Action
dated August 28, 2002. Please amend the above-identified application as follows:

IN THE CLAIMS:

Please cancel claims 2, 5, 6 and 14-18 in their entirety without prejudice or disclaimer of
the subject matter amend claims 1, 3, 4, 7 and 9 as follows:

1. (Amended) A semiconductor device, comprising:

a first metallization layer;

a first diffusion barrier layer disposed over said first metallization layer;

a first etch stop layer disposed over and spaced from said first diffusion barrier layer;

a dielectric layer disposed over said second etch stop layer;

a via extending through said dielectric layer, said first etch stop layer, and said first
diffusion barrier layer; and

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